

IN THE CLAIMS

1. (currently amended) A heat treatment jig for a semiconductor substrate that is mounted on a heat treatment boat of a vertical heat treatment furnace, comprising:
  - a semiconductor substrate that is heat treated;
  - a first jig that is constituted of a silicon material and comes into direct contact with the semiconductor substrate to support; and
  - a second jig (holder) that holds the first jig and is mounted on the heat treatment boat, wherein the first jig is placed on the second [[jug]] jig so that the first jig is movable relative to the second jig on the surface of the second jig.

2. (previously presented) The heat treatment jig for a semiconductor substrate according to Claim 1:

wherein the first jig has, in a region that comes into direct contact with the semiconductor substrate, a thickness in the range of from 0.5 to 10 mm, the surface roughness in the range of from 0.02 to 10  $\mu\text{m}$  and the flatness of 100  $\mu\text{m}$  or less; and

the second jig has, in a region that comes into direct contact with the first jig, a thickness in the range of from 0.5 to 10 mm, the surface roughness in the range of from 0.02 to 10  $\mu\text{m}$  and the flatness of 200  $\mu\text{m}$  or less.

3. (previously presented) The heat treatment jig for a semiconductor substrate according to Claim 1:

wherein the first jig is 0.5 mm or more in a width that comes into direct contact with the semiconductor substrate.

4. (previously presented) The heat treatment jig for a semiconductor substrate according to Claim 2:

wherein the first jig is 0.5 mm or more in a width that comes into direct contact with the semiconductor substrate.

5. (withdrawn) A heat treatment jig for a semiconductor substrate according to Claim 1:

wherein in the first jig, on a surface of a region that comes into direct contact with the semiconductor substrate, any one of a silicon carbide film, an oxide film or a poly-silicon film is formed.

6. canceled

7. canceled

8. (withdrawn) A heat treatment jig for a semiconductor substrate according to Claim 2:

wherein in the first jig, on a surface of a region that comes into direct contact with the semiconductor substrate, any one of a silicon carbide film, an oxide film or a poly-silicon film is formed.

9. (withdrawn) A heat treatment jig for a semiconductor substrate according to Claim 3:

wherein in the first jig, on a surface of a region that comes into direct contact with the semiconductor substrate, any one of a silicon carbide film, an oxide film or a poly-silicon film is formed.

10. (withdrawn) A heat treatment jig for a semiconductor substrate according to Claim 4:

wherein in the first jig, on a surface of a region that comes into direct contact with the semiconductor substrate, any one of a silicon carbide film, an oxide film or a poly-silicon film is formed.